

## **STTH6002C**

## High efficiency ultrafast diode

### Main product characteristics

I <sub>F(AV)</sub>	2 x 30 A
V <sub>RRM</sub>	200 V
T <sub>j</sub> (max)	175° C
V <sub>F</sub> (typ)	0.75 V
t <sub>rr</sub> (typ)	22 ns

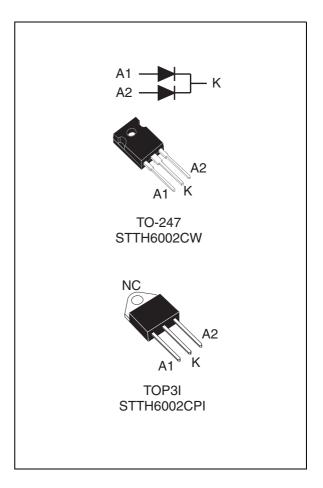
#### Features and benefits

- Suited for SMPS
- Low losses
- Low forward and reverse recovery times
- High surge current capability
- High junction temperature

### **Description**

Dual center tab rectifier suited for switch mode power supplies and high frequency DC to DC converters.

Packaged in TO-247 and TOP3I, this device is intended for use in low voltage, high frequency inverters, free wheeling and polarity protection



#### **Order codes**

Part Number	Marking
STTH6002CW	STTH6002C
STTH6002CPI	STTH6002C

Characteristics STTH6002C

### 1 Characteristics

Table 1. Absolute ratings (limiting values at  $T_i = 25^{\circ}$  C, unless otherwise specified)

Symbol	Parameter			Value	Unit
V <sub>RRM</sub>	Repetitive peak reverse voltage			200	٧
I <sub>F(RMS)</sub>	RMS forward current			50	Α
		TO-247	Per diode T <sub>c</sub> = 140° C	30	
I <sub>F(AV)</sub> Average forward current, &			Per device T <sub>c</sub> = 125° C	60	
	Average forward current, $\delta = 0.5$		Per diode T <sub>c</sub> = 120° C	30	Α
		TOP3I	Per device T <sub>c</sub> = 105° C	60	
I <sub>FSM</sub>	Surge non repetitive forward current $t_p = 10 \text{ ms Sinusoidal}$			330	Α
T <sub>stg</sub>	Storage temperature range			-65 to +175	° C
T <sub>j</sub>	Maximum operating junction temperature			175	° C

Table 2. Thermal parameters

Symbol	Parameter			Value	Unit
		TO-247	Per diode	1.2	
В	D. honetien to come	10-247	Total	0.8	
$R_{th(j-c)}$ Junction to case	TOPOL	Per diode	1.8	° C/M	
		TOP3I	Total	1.20	° C/W
0	Caurdina	TO-247		0.4	
R <sub>th(c)</sub> Coupling		TOP3I		0.6	

When the two diodes 1 and 2 are used simultaneously:

 $\Delta Tj(diode\ 1) = P\ (diode\ 1)\ X\ R_{th(j\text{-}c)}\ (Per\ diode) + P\ (diode\ 2)\ x\ R_{th(c)}$ 

STTH6002C Characteristics

Table 3. Static electrical characteristics

Symbol	Parameter	Test conditions		Тур	Max.	Unit
I <sub>R</sub> <sup>(1)</sup> Reverse leakage current	Deverse leekege eurrent	T <sub>j</sub> = 25° C	$V_R = V_{RRM}$		30	μΑ
	Theverse leakage current	T <sub>j</sub> = 125° C		30	300	
	$T_{j} = 25^{\circ} \text{ C}$	T - 25° C	I <sub>F</sub> = 30 A		1.05	
V <sub>F</sub> <sup>(2)</sup>		1	I <sub>F</sub> = 60 A		1.18	V
V <sub>F</sub> <sup>(2)</sup> Forward voltage drop	T 4500 O	I <sub>F</sub> = 30 A	0.75	0.84	V	
	T <sub>j</sub> = 150° C	I <sub>F</sub> = 60 A	0.9	0.99		

- 1. Pulse test:  $t_p$  = 5 ms,  $\delta$  < 2 %
- 2. Pulse test:  $t_p$  = 380  $\mu$ s,  $\delta$  < 2 %

To evaluate the conduction losses use the following equation:

 $P = 0.69 \text{ x } I_{F(AV)} + 0.005 I_{F}^{2}_{(RMS)}$ 

Table 4. Dynamic characteristics

Symbol	Parameter	Test conditions	Тур	Max.	Unit
t <sub>rr</sub>	Reverse recovery time	$I_F = 1 \text{ A, } dI_F/dt = 200 \text{ A/}\mu\text{s,}$ $V_R = 30 \text{ V, } T_j = 25 \text{ °C}$	22	27	ns
I <sub>RM</sub>	Reverse recovery current	$I_F = 30 \text{ A}, dI_F/dt = 200 \text{ A}/\mu\text{s}, \ V_R = 160 \text{ V}, T_j = 125 ^{\circ}\text{C}$	7.6	9.5	А
t <sub>fr</sub>	Forward recovery time	$I_F = 30 \text{ A}, dI_F/dt = 200 \text{ A/}\mu\text{s}$ $V_{FR} = 1.1 \text{ x } V_{Fmax}, T_j = 25 \text{ °C}$		220	ns
V <sub>FP</sub>	Forward recovery voltage	$I_F = 30 \text{ A}, dI_F/dt = 200 \text{ A/}\mu\text{s},$ $T_j = 25 ^{\circ}\text{C}$	2.5		V

Figure 1. Peak current versus duty cycle (per diode)

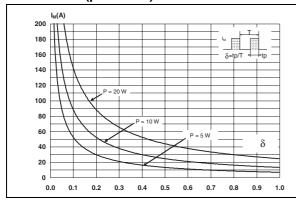
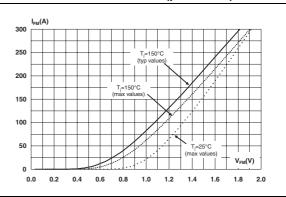


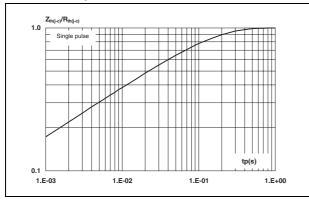
Figure 2. Forward voltage drop versus forward current (per diode)



Characteristics STTH6002C

Figure 3. Relative variation of thermal impedance junction to case versus pulse duration

Figure 4. Junction capacitance versus reverse applied voltage (typical values)



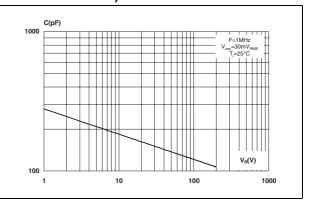
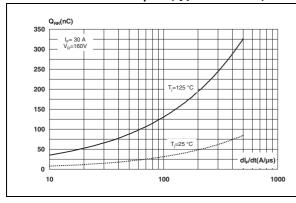


Figure 5. Reverse recovery charges versus dl<sub>F</sub>/dt (typical values)

Figure 6. Reverse recovery time versus  $dI_F/dt$  (typical values)



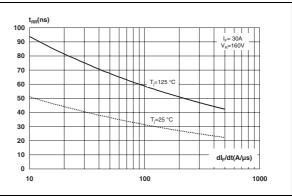
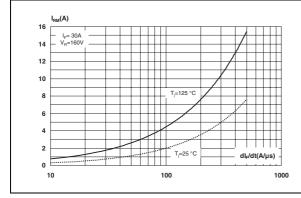
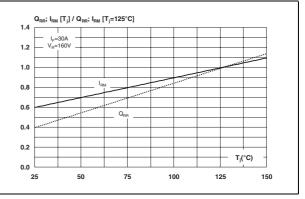


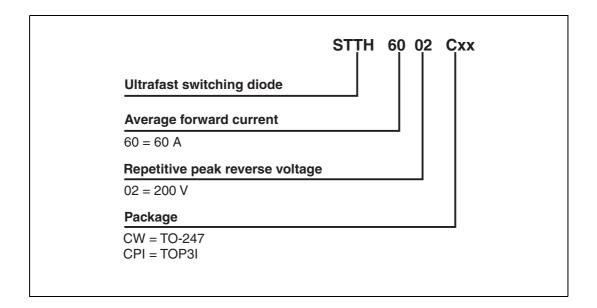
Figure 7. Peak reverse recovery current versus dl<sub>F</sub>/dt (typical values)

Figure 8. Dynamic parameters versus junction temperature





## 2 Ordering information scheme



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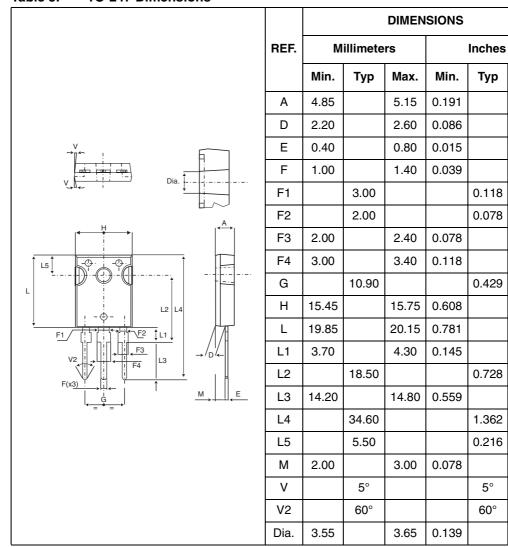
Package information STTH6002C

## 3 Package information

Epoxy meets UL94, V0

Cooling method: by conduction (C)
Recommended torque value: 0.8 Nm
Maximum torque value: 1.0 Nm

Table 5. TO-247 Dimensions



Max.

0.203

0.102

0.031

0.055

0.094

0.133

0.620

0.793

0.169

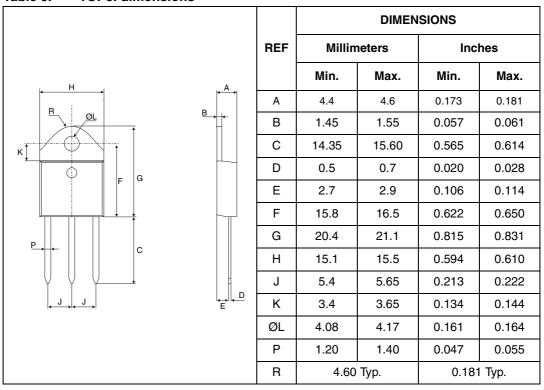
0.582

0.118

0.143

STTH6002C Package information

Table 6. TOP3I dimensions



In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com.

Ordering information STTH6002C

# 4 Ordering information

Part Number	Marking	Package	Weight	Base qty	Delivery mode
STTH6002CW	STTH6002C	TO-247	4.46 g	30	Tube
STTH6002CPI	STTH6002C	TOP3I	4.7 g	30	Tube

# 5 Revision history

Date	Revision	Description of Changes
Feb-2004	1	First issue
05-Apr-2006	2	Reformatted to current template. Package TOP3I added.

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